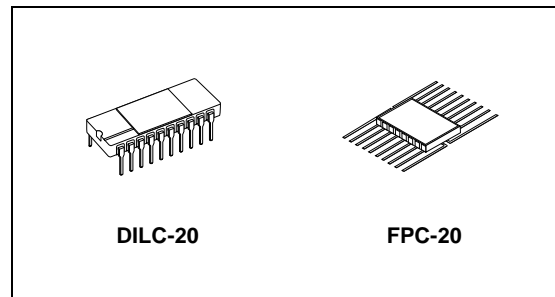




# M54HC241

## RAD-HARD OCTAL BUS BUFFER WITH 3 STATE OUTPUTS (NON INVERTED)

- HIGH SPEED:  
 $t_{PD} = 10\text{ns}$  (TYP.) at  $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 4\mu\text{A}$ (MAX.) at  $T_A=25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 6\text{mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \cong t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:  
 $V_{CC}$  (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 54 SERIES 241
- SPACE GRADE-1: ESA SCC QUALIFIED
- 50 krad QUALIFIED, 100 krad AVAILABLE ON REQUEST
- NO SEL UNDER HIGH LET HEAVY IONS IRRADIATION
- DEVICE FULLY COMPLIANT WITH SCC-9401-035



### ORDER CODES

PACKAGE	FM	EM
DILC	M54HC241D	M54HC241D1
FPC	M54HC241K	M54HC241K1

Each  $\overline{G}$  and  $\overline{G}$  control inputs governs four BUS BUFFERS.

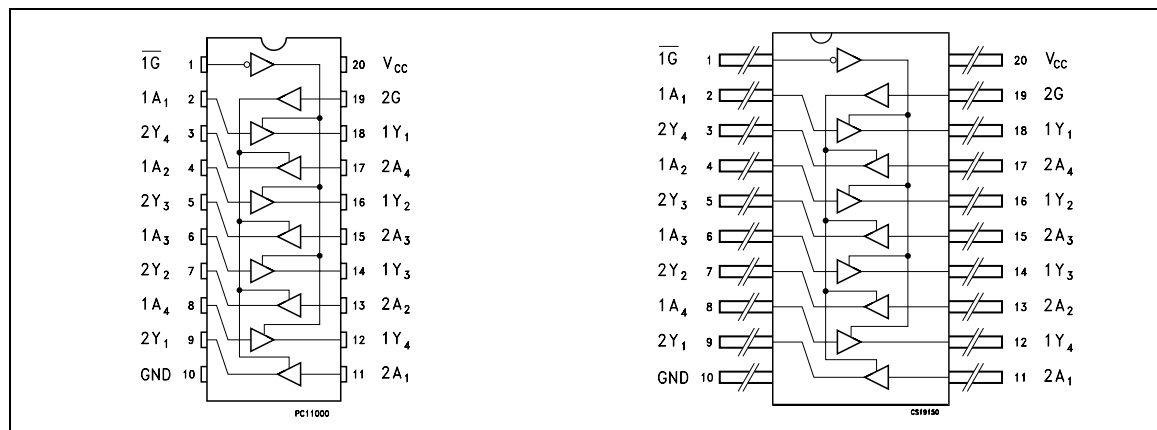
This device is designed to be used with 3 state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### DESCRIPTION

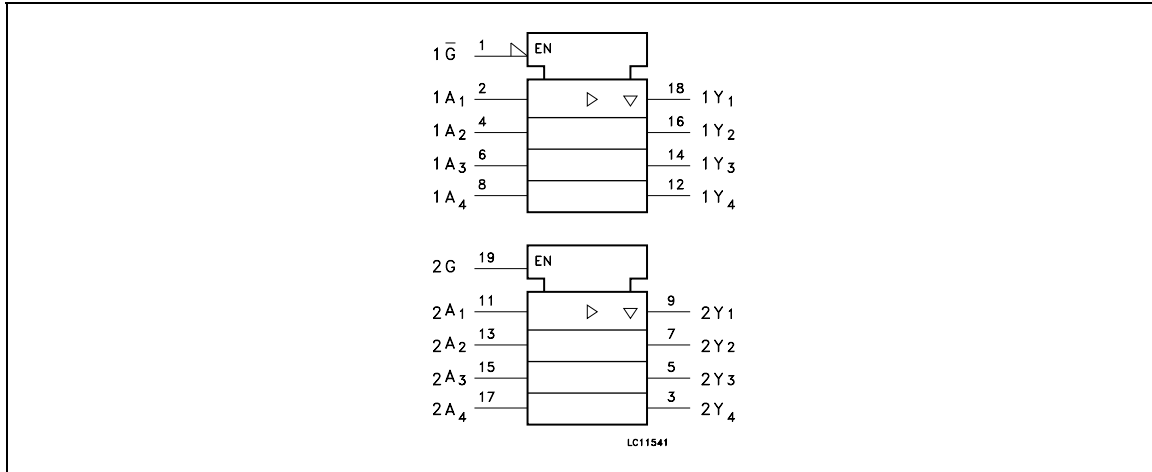
The 54HC241 is an advanced high-speed CMOS OCTAL BUS BUFFER (3-STATE) fabricated with silicon gate C<sup>2</sup>MOS technology.

### PIN CONNECTION

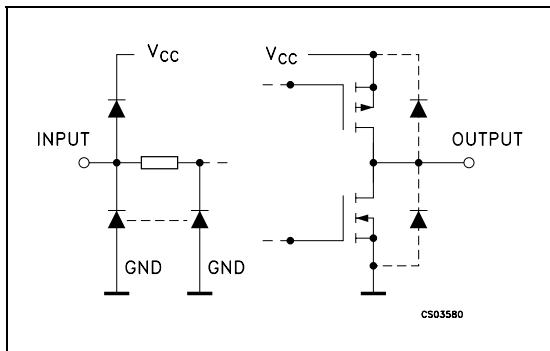


# M54HC241

## IEC LOGIC SYMBOLS



## INPUT AND OUTPUT EQUIVALENT CIRCUIT



## PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1	1G	Output Enable Input
2, 4, 6, 8	1A1 to 1A4	Data Inputs
9, 7, 5, 3	2Y1 to 2Y4	Data Outputs
11, 13, 15, 17	2A1 to 2A4	Data Inputs
18, 16, 14, 12	1Y1 to 1Y4	Data Outputs
19	2G	Output Enable Input
10	GND	Ground (0V)
20	V <sub>CC</sub>	Positive Supply Voltage

## TRUTH TABLE

INPUTS		OUTPUT	INPUTS		OUTPUT
1G-bar	1An	1Yn	2G	2An	2Yn
L	L	L	H	L	L
L	H	H	H	H	H
H	X	Z	L	X	Z

X : Don't Care  
Z : High Impedance

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	-0.5 to +7	V
$V_I$	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_O$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$\pm 20$	mA
$I_{OK}$	DC Output Diode Current	$\pm 20$	mA
$I_O$	DC Output Current	$\pm 35$	mA
$I_{CC}$ or $I_{GND}$	DC $V_{CC}$ or Ground Current	$\pm 70$	mA
$P_D$	Power Dissipation	420	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	265	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
$V_{CC}$	Supply Voltage	2 to 6	V	
$V_I$	Input Voltage	0 to $V_{CC}$	V	
$V_O$	Output Voltage	0 to $V_{CC}$	V	
$T_{op}$	Operating Temperature	-55 to 125	°C	
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V <sub>OH</sub>	High Level Output Voltage	2.0	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I <sub>O</sub> =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I <sub>O</sub> =-6.0 mA	4.18	4.31		4.13		4.10		
		6.0	I <sub>O</sub> =-7.8 mA	5.68	5.8		5.63		5.60		
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		6.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		4.5	I <sub>O</sub> =6.0 mA		0.17	0.26		0.33		0.40	
		6.0	I <sub>O</sub> =7.8 mA		0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	μA
I <sub>OZ</sub>	High Impedance Output Leakage Current	6.0	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = V <sub>CC</sub> or GND			± 0.5		± 5		± 10	μA
I <sub>CC</sub>	Quiescent Supply Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			4		40		80	μA

AC ELECTRICAL CHARACTERISTICS ( $C_L = 50$  pF, Input  $t_r = t_f = 6$  ns)

Symbol	Parameter	Test Condition			Value						Unit	
		$V_{CC}$ (V)	$C_L$ (pF)		$T_A = 25^\circ\text{C}$			$-40$ to $85^\circ\text{C}$		$-55$ to $125^\circ\text{C}$		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$t_{TLH}$ $t_{THL}$	Output Transition Time	2.0	50		25	60		75		90	ns	
		4.5		7	12		19		18			
		6.0		6	10		13		15			
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time	2.0	50		36	90		115		135	ns	
		4.5		12	18		23		27			
		6.0		10	15		20		23			
		2.0	150		51	130		165		195	ns	
		4.5		17	26		33		39			
		6.0		14	22		28		33			
$t_{PZL}$ $t_{PZH}$	High Impedance Output Enable Time	2.0	50	$R_L = 1\text{ K}\Omega$	48	125		155		190	ns	
		4.5			16	25		31		38		
		6.0			14	21		25		32		
		2.0	150	$R_L = 1\text{ K}\Omega$	63	165		205		250	ns	
		4.5			21	33		41		50		
		6.0			18	28		35		43		
$t_{PLZ}$ $t_{PHZ}$	High Impedance Output Disable Time	2.0	50	$R_L = 1\text{ K}\Omega$	32	125		155		190	ns	
		4.5			15	25		31		38		
		6.0			14	21		26		32		

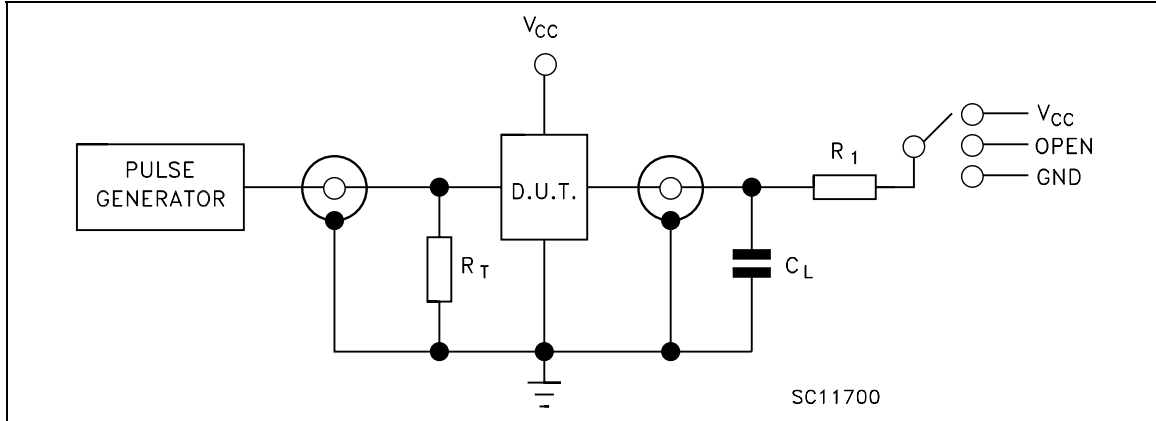
## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition			Value						Unit	
		$V_{CC}$ (V)			$T_A = 25^\circ\text{C}$			$-40$ to $85^\circ\text{C}$		$-55$ to $125^\circ\text{C}$		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$C_{IN}$	Input Capacitance	5.0				5	10		10		10	pF
$C_{OUT}$	Output Capacitance	5.0				10						pF
$C_{PD}$	Power Dissipation Capacitance (note 1)	5.0				33						pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$  (per circuit)

# M54HC241

## TEST CIRCUIT



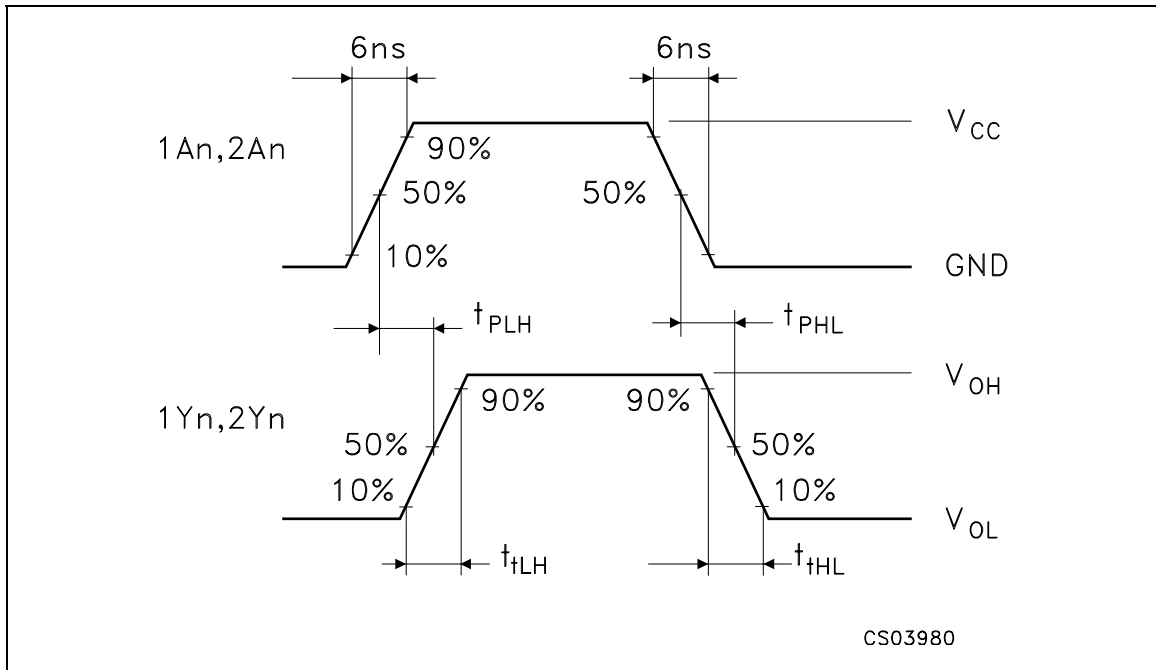
TEST	SWITCH
$t_{PLH}$ , $t_{PHL}$	Open
$t_{PZL}$ , $t_{PLZ}$	$V_{CC}$
$t_{PZH}$ , $t_{PHZ}$	GND

$C_L$  = 50pF/150pF or equivalent (includes jig and probe capacitance)

$R_1$  = 1K $\Omega$  or equivalent

$R_T$  =  $Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

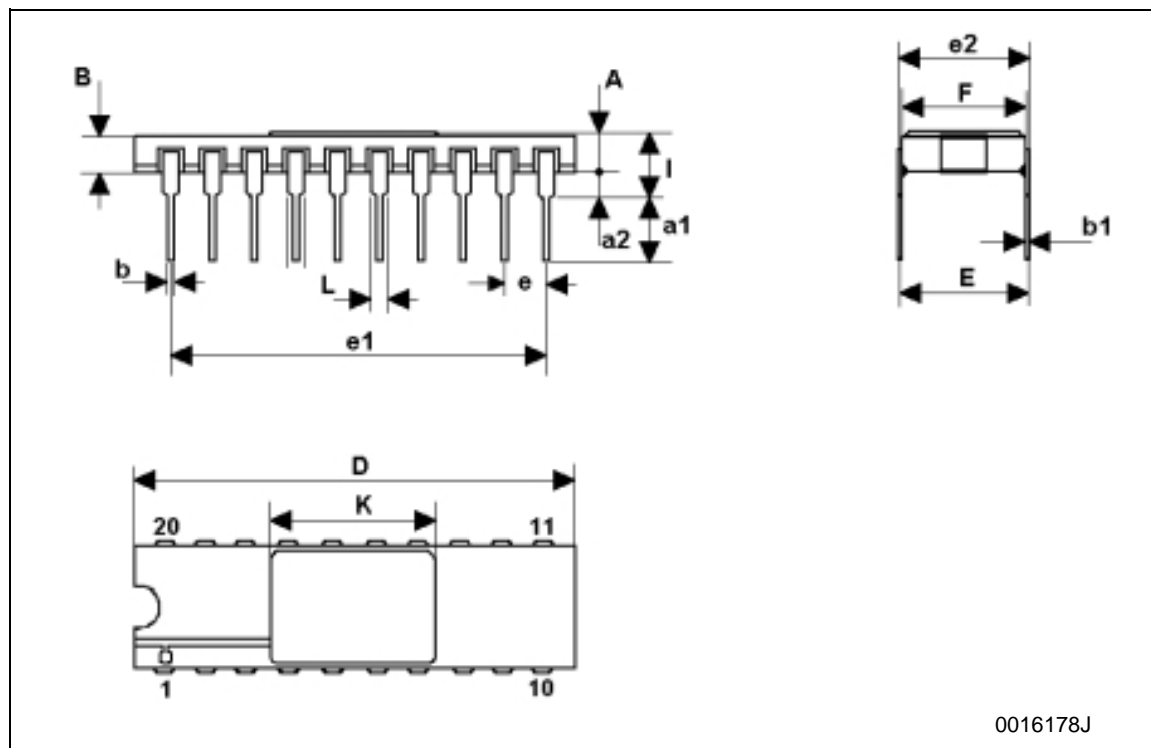
## WAVEFORM 1: PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)





## DILC-20 MECHANICAL DATA

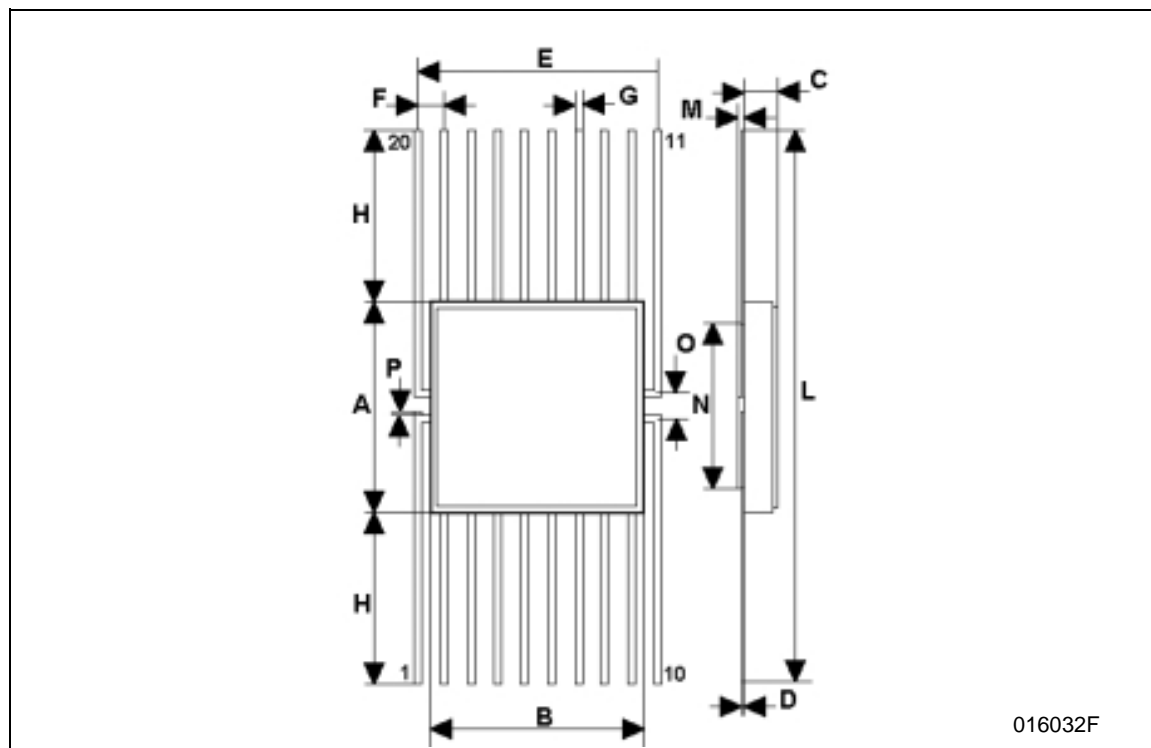
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.1		2.71	0.083		0.107
a1	3.00		3.70	0.118		0.146
a2	0.63	0.88	1.14	0.025	0.035	0.045
B	1.93	2.03	2.23	0.076	0.080	0.088
b	0.40	0.45	0.50	0.016	0.018	0.020
b1	0.20	0.254	0.30	0.008	0.010	0.012
D	25.14	25.40	25.65	0.990	1.000	1.010
e	7.36	7.62	7.87	0.290	0.300	0.310
e1		2.54			0.100	
e2	22.73	22.86	22.99	0.895	0.900	0.905
e3	7.62	7.87	8.12	0.300	0.310	0.320
F	7.29	7.49	7.70	0.287	0.295	0.303
l			3.86			0.152
K	11.30		11.56	0.445		0.455
L	1.14	1.27	1.40	0.045	0.050	0.055





## FPC-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.98	10.16	10.34	0.393	0.400	0.407
B	9.98	10.16	10.34	0.393	0.400	0.407
C	1.45	1.61	1.78	0.57	0.63	0.070
D	0.10	0.127	0.18	0.004	0.005	0.007
E	11.30	11.43	11.56	0.445	0.450	0.455
F		1.27			0.050	
G	0.38	0.43	0.48	0.015	0.017	0.019
H	7.24		8.16	0.285		0.320
L	24.46		26.67	0.960		1.050
M	0.45	0.50	0.55	0.018	0.020	0.022
N		7.87			0.310	
O	1.14	1.27	1.40	0.045	0.050	0.055
P	0.10	0.18	0.25	0.004	0.007	0.010



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